

SPECIFIC SITE BACKSIDE UNDERLAYING AND MICROMASKING METHOD FOR ELECTRICAL CHARACTERIZATION OF SEMICONDUCTOR DEVICES

Abstract

A method for implementing backside probing of a semiconductor device includes isolating an identified defect area on a backside of the semiconductor device, and milling the identified defect area to an initial depth. Edges of the identified defect area are masked, wherein unmasked semiconductor material, beginning at the initial depth, is etched for a plurality of timed intervals until one or more active devices are reached. The one or more active devices are electrically probed.